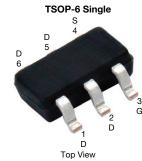
Si3464DV

www.vishay.com

Vishay Siliconix



Marking code: AZ

PRODUCT SUMMARY					
V _{DS} (V)	20				
$R_{DS(on)}$ max. (Ω) at V_{GS} = 4.5 V	0.024				
$R_{DS(on)}$ max. (Ω) at V_{GS} = 2.5 V	0.028				
$R_{DS(on)}$ max. (Ω) at V_{GS} = 1.8 V	0.030				
Q _g typ. (nC)	11				
I _D (A) ^{a, e}	8				
Configuration	Single				

FEATURES

N-Channel 20 V (D-S) MOSFET

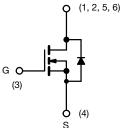
- TrenchFET[®] power MOSFET
- 100 % R_g tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- DC/DC converters
- Load switch for portable applications



RoHS COMPLIANT HALOGEN



D

N-Channel MOSFET

ORDERING INFORMATION

Package	TSOP-6
Lead (Pb)-free and halogen-free	Si3464DV-T1-GE3

PARAMETER Drain-source voltage		SYMBOL	LIMIT	UNIT	
		V _{DS}	20	N	
Gate-source voltage		V _{GS}	± 8	V	
	T _C = 25 °C		8 ^a		
Operation of the intervent (T 150 °C)	T _C = 70 °C		8 a		
Continuous drain current ($T_J = 150 \ ^\circ C$)	T _A = 25 °C	I _D	7.5 ^{b, c}		
	T _A = 70 °C		6 ^{b, c}	A	
Pulsed drain current		I _{DM}	20		
	T _C = 25 °C		3		
Continuous source-drain diode current	T _A = 25 °C	I _S	1.7 ^{b, c}		
	T _C = 25 °C		3.6		
Maximum power dissipation	T _C = 70 °C		2.3	w	
	T _A = 25 °C	P _D	2 ^{b, c}	VV	
	T _A = 70 °C		1.3 ^{b, c}		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature)			260	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient b, d	t ≤ 5 s	R _{thJA}	50	62.5	°C/W
Maximum junction-to-foot (drain)	Steady state	R _{thJF}	28	35	C/W

Notes

a. Package limited

b. Surface mounted on 1" x 1" FR4 board

c. t = 5 s

d. Maximum under steady state conditions is 110 °C/W

e. Based on $T_C = 25 \ ^{\circ}C$

S10-0218-Rev. A, 25-Jan-10

1

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PARAMETER SYMBOL TEST CONE		TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	· · · · ·					
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	20	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	L 050 A	-	23	-	
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-2.6	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	0.45	-	1	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$	-	-	± 100	nA
Zere gete veltage drein eurrent		$V_{DS} = 20 V, V_{GS} = 0 V$	-	-	1	μA
Zero gate voltage drain current	IDSS	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 70 ^{\circ}\text{C}$	-	-	10	
On-state drain current ^a	I _{D(on)}	$V_{DS}{\leq}5$ V, $V_{GS}{=}4.5$ V	20	-	-	A
Drain-source on-state resistance ^a		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 7.5 \text{ A}$	-	0.020	0.024	
	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 7 \text{ A}$	-	0.023	0.028	Ω
		$V_{GS} = 1.8 \text{ V}, I_D = 6.7 \text{ A}$	-	0.025	0.030	
Forward transconductance ^a	g fs	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 7.5 \text{ A}$	-	17	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	1065	-	pF
Output capacitance	Coss	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	-	150	-	
Reverse transfer capacitance	C _{rss}		-	70	-	
Total gata abarga	0	V_{DS} = 10 V, V_{GS} = 5 V, I_{D} = 7.5 A	-	12	18	nC
Total gate charge	Qg		-	11	17	
Gate-source charge	Q _{gs}	V_{DS} = 10 V, V_{GS} = 4.5 V, I_{D} = 7.5 A	-	1.8	-	
Gate-drain charge	Q _{gd}		-	1.1	-	
Gate resistance	Rg	f = 1 MHz	0.4	2.2	4.4	Ω
Turn-on delay time	t _{d(on)}		-	5	10	
Rise time	t _r	V_{DD} = 10 V, R_L = 1.7 Ω	-	15	23	
Turn-off delay time	t _{d(off)}	$I_D \cong 6$ A, V_{GEN} = 4.5 V, R_g = 1 Ω	-	43	65	
Fall time	t _f		-	10	20	
Turn-on delay time	t _{d(on)}		-	3	6	ns
Rise time	tr	V_{DD} = 10 V, R_L = 1.7 Ω	-	12	18	
Turn-off delay time	t _{d(off)}	$I_D \cong 6$ A, V_{GEN} = 5 V, R_g = 1 Ω	-	22	33	
Fall time	t _f		-	8	16	
Drain-Source Body Diode Characteristi	cs					
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	3	_
Pulse diode forward current	I _{SM}		-	-	20	A
Body diode voltage	V _{SD}	$I_{\rm S} = 6$ A, $V_{\rm GS} = 0$ V	-	0.75	1.2	V
Body diode reverse recovery time	t _{rr}		-	15	23	ns
Body diode reverse recovery charge	Q _{rr}	I _F = 6 A, di/dt = 100 A/μs,	-	6	12	nC
Reverse recovery fall time	t _a	$T_{\rm J} = 25 \ ^{\circ}{\rm C}$	-	8	-	
Reverse recovery rise time	t _b		-	7	-	ns

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2%

b. Guaranteed by design, not subject to production testing

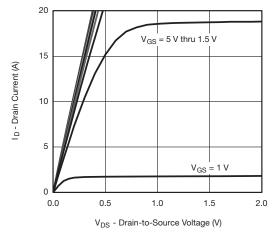
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

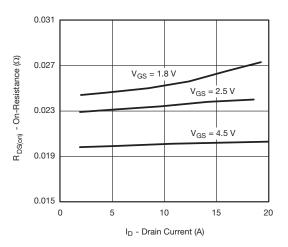


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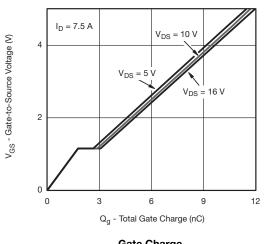
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



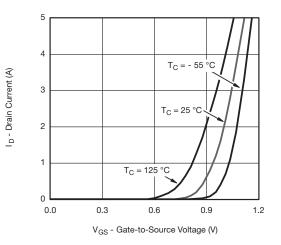




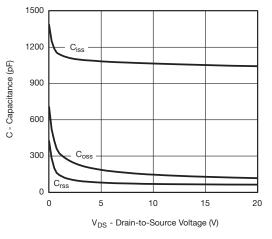
On-Resistance vs. Drain Current and Gate Voltage



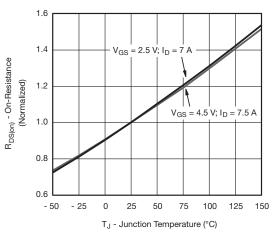




Transfer Characteristics







On-Resistance vs. Junction Temperature

S10-0218-Rev. A, 25-Jan-10

3

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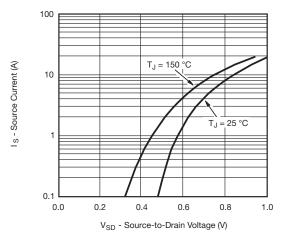
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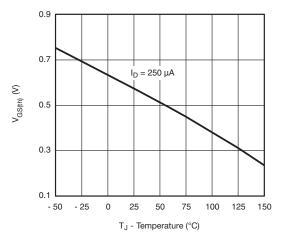
Si3464DV

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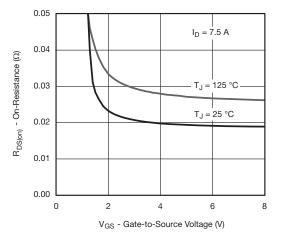
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



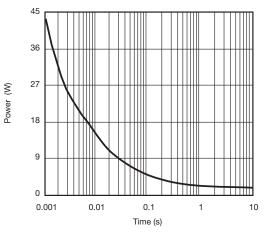
Source-Drain Diode Forward Voltage



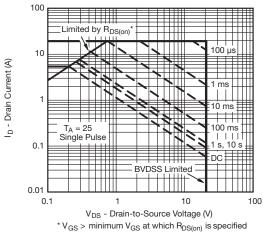




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power (Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient

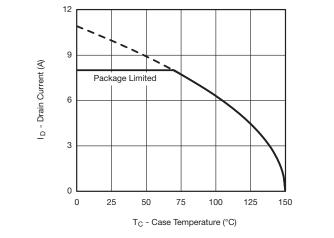
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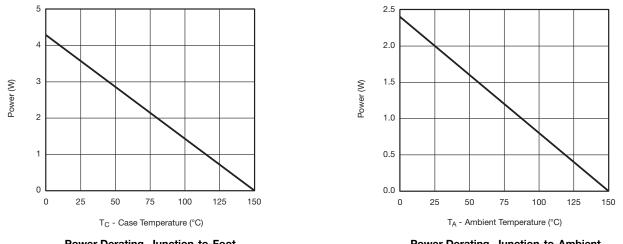


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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)







Power Derating, Junction-to-Foot



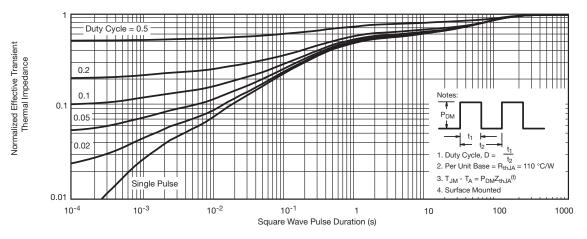
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

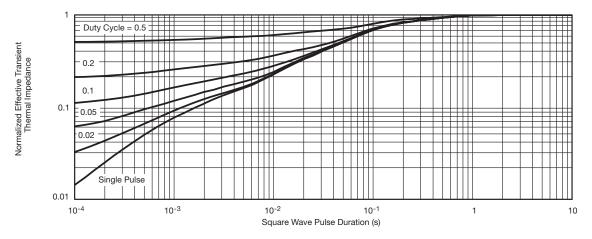


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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for silicon technology and package reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65712.



Package Information

Vishay Siliconix

TSOP: 5/6-LEAD JEDEC Part Number: MO-193C









6-LEAD TSOP



	MILLIMETERS			INCHES				
Dim	Min	Nom	Max	Min	Nom	Max		
Α	0.91	-	1.10	0.036	-	0.043		
A ₁	0.01	-	0.10	0.0004	-	0.004		
A ₂	0.90	-	1.00	0.035	0.038	0.039		
b	0.30	0.32	0.45	0.012	0.013	0.018		
С	0.10	0.15	0.20	0.004	0.006	0.008		
D	2.95	3.05	3.10	0.116	0.120	0.122		
Е	2.70	2.85	2.98	0.106	0.112	0.117		
E ₁	1.55	1.65	1.70	0.061	0.065	0.067		
е	0.95 BSC			0.0374 BSC				
e ₁	1.80	1.90	2.00	0.071	0.075	0.079		
L	0.32	-	0.50	0.012	-	0.020		
L ₁		0.60 Ref			0.024 Ref			
L ₂	0.25 BSC				0.010 BSC			
R	0.10	-	-	0.004	-	-		
θ	0°	4°	8°	0°	4°	8°		
θ_1	7° Nom				7° Nom			
		ev. I, 18-Dec	c-06		ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540			

PAD Pattern



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Recommended Land Pattern For TSOP-5L / TSOP-6L





TSOP 5L





Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022	
DWG: 3010	

1



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1